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TITLE: Method for manufacturing capacitor

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PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
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APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
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INT-CL (IPC): H01L027/04

ABSTRACTED-PUB-NO: KR2002045261A

BASIC-ABSTRACT:

NOVELTY - A fabrication method of capacitors is provided to prevent an etch damage of a **Pt seed** and to simplify manufacturing processes by using an organic substance as a sacrificial layer.

DETAILED DESCRIPTION - After forming an interlayer dielectric(12) having a contact hole on a silicon substrate(11), a contact plug(13) is formed. A **Pt seed**(14a) is formed on the resultant structure. An organic substance having a low dielectric constant and a high adhesive force with the Pt is formed on the

Pt seed(14a) without forming a glue layer. After exposing the surface of the **Pt seed**, a Pt growing film(14b) is grown on the **Pt seed** by an ECD(Electro Chemical Deposition), thereby forming a lower electrode(14) including the **Pt seed**(14a) and the Pt growing film(14b). After removing the organic substance, a dielectric film(17) and an upper electrode(18) are sequentially formed on the resultant structure.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: METHOD MANUFACTURE CAPACITOR

DERWENT-CLASS: L03 U11

CPI-CODES: L04-C13B; L04-C14;

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